

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-00152A-B

2. Structure :

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :
 Top side (Anode) : Aluminum alloy .
 Back side (Cathode) : Gold .

3. Size :

- 3-1. Chip size : 196.8 mils x 118.1 mils (5 mm x 3 mm).
- 3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
- 3-3. Active area : 187.4 mils x 108.6 mils (4.76 mm x 2.76 mm).
- 3-4. Left & Right side Bonding pad (Anode) : 5.1 mils x 5.1 mils (0.13 mm x 0.13 mm).
- 3-5. Center Bonding pad (Anode) : 5.1 mils x 5.1 mils (0.13 mm x 0.13 mm).
- 3-6. Pattern drawing : Refer to the attached drawing

4. Electro-optical characteristics (Ta = 25 °C)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|----------------------------|--------|------------------------------------|------|------|------|------|
| *Reverse dark Current | ID | VR=10V Ee=0mW/cm ² | | | 30 | nA |
| *Reverse breakdown voltage | V(BR)R | IR=100uA Ee=0mW/cm ² | 40 | | | V |
| *Forward voltage | VF | IF=10mA Ee=0mW/cm | | | 1.2 | V |

*Based on 100% probing.

